

# Steven A Vitale

## List of Publications by Year in descending order

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Version: 2024-02-01

26  
papers

1,305  
citations

777949

13  
h-index

799663

21  
g-index

27  
all docs

27  
docs citations

27  
times ranked

1862  
citing authors

#	ARTICLE	IF	CITATIONS
1	Multi-Level Electro-Thermal Switching of Optical Phase-Change Materials Using Graphene. <i>Advanced Photonics Research</i> , 2021, 2, 2000034.	1.7	75
2	Transient Tap Couplers for Wafer-Level Photonic Testing Based on Optical Phase Change Materials. <i>ACS Photonics</i> , 2021, 8, 1903-1908.	3.2	24
3	Electrically-switchable foundry-processed phase change photonic devices. , 2021, , .		5
4	Interface State Reduction by Plasma-Enhanced Atomic Layer Deposition of Homogeneous Ternary Oxides. <i>ACS Applied Materials &amp; Interfaces</i> , 2020, 12, 43250-43256.	4.0	2
5	Valleytronics: Opportunities, Challenges, and Paths Forward. <i>Small</i> , 2018, 14, e1801483.	5.2	221
6	A 1.3 $\mu$ W, 5pj/cycle sub-threshold MSP430 processor in 90nm xLP FDSOI for energy-efficient IoT applications. , 2016, , .		7
7	Comparison of gate dielectric plasma damage from plasma-enhanced atomic layer deposited and magnetron sputtered TiN metal gates. <i>Journal of Applied Physics</i> , 2015, 118, .	1.1	18
8	Robust subthreshold level conversion. , 2015, , .		0
9	Low voltage devices and circuits for energy-starved systems. , 2015, , .		0
10	Gadolinium oxide coated fully depleted silicon-on-insulator transistors for thermal neutron dosimetry. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2013, 721, 45-49.	0.7	4
11	Etching selectivity of indium tin oxide to photoresist in high density chlorine- and ethylene-containing plasmas. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013, 31, 021210.	0.6	6
12	Plasma-enhanced atomic layer deposition and etching of high- <i>k</i> gadolinium oxide. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2012, 30, .	0.9	9
13	SOI circuits powered by embedded solar cell. , 2011, , .		2
14	Work-Function-Tuned TiN Metal Gate FDSOI Transistors for Subthreshold Operation. <i>IEEE Transactions on Electron Devices</i> , 2011, 58, 419-426.	1.6	102
15	The effects of low temperature and pressure on the fracture behaviors of organosilicate thin films. <i>Journal of Materials Research</i> , 2011, 26, 2524-2532.	1.2	3
16	FDSOI Process Technology for Subthreshold-Operation Ultra-Low-Power Electronics. <i>ECS Transactions</i> , 2011, 35, 179-188.	0.3	2
17	FDSOI Process Technology for Subthreshold-Operation Ultralow-Power Electronics. <i>Proceedings of the IEEE</i> , 2010, 98, 333-342.	16.4	84
18	High density plasma etching of titanium nitride metal gate electrodes for fully depleted silicon-on-insulator subthreshold transistor integration. <i>Journal of Vacuum Science &amp; Technology B</i> , 2009, 27, 2472-2479.	1.3	11

#	ARTICLE	IF	CITATIONS
19	Liquid Droplet Dispersions Formed by Homogeneous Liquid-Liquid Nucleation: "The Ouzo Effect". Langmuir, 2003, 19, 4105-4110.	1.6	398
20	Silicon dioxide etching yield measurements with inductively coupled fluorocarbon plasmas. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2003, 21, 381-387.	0.9	30
21	Etching of organosilicate glass low-k dielectric films in halogen plasmas. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2002, 20, 651-660.	0.9	33
22	Plasma surface kinetics and simulation of feature profile evolution in Cl <sub>2</sub> +HBr etching of polysilicon. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2002, 20, 2106.	0.9	98
23	Silicon etching yields in F <sub>2</sub> , Cl <sub>2</sub> , Br <sub>2</sub> , and HBr high density plasmas. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2001, 19, 2197-2206.	0.9	106
24	Etching chemistry of benzocyclobutene (BCB) low-k dielectric films in F <sub>2</sub> +O <sub>2</sub> and Cl <sub>2</sub> +O <sub>2</sub> high density plasmas. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2000, 18, 2770-2778.	0.9	40
25	Abatement of C <sub>2</sub> F <sub>6</sub> in rf and microwave plasma reactors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2000, 18, 2217.	0.9	14
26	Decomposition of ethyl chloride and vinyl chloride in an electron beam generated plasma reactor. Radiation Physics and Chemistry, 1997, 49, 421-428.	1.4	10